Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO.		SERIAL NO.		
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LIST OF	REFE	RENCES CITED BY AP	PLICANT	Hitoshi SAKAMOTO, et al.				
				FILING DATE		GROUP		
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB	FILING DATE IF APPROPRIATE	
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H	AO	2000-133710	05/12/00	Japan		YES	S NO	
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Form PTO 1449		U.S. DEPARTMENT	MMERCE	ATTY DOCKET NO.	SERIAL NO. 10/665,473			
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